

STARPOWER

SEMICONDUCTOR

IGBT

GD100HFF120C1S

1200V/100A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra switching speed as well as short circuit ruggedness. They are designed for the applications such as electronic welder and inductive heating.

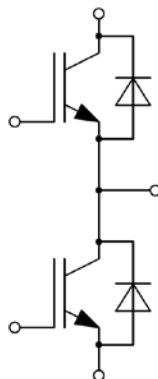
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- $V_{CE(sat)}$ with positive temperature coefficient
- Low switching losses
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Switching mode power supply
- Inductive heating
- Electronic welder

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	149	A
	@ $T_C=85^{\circ}\text{C}$	100	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	511	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.90	2.35	V	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.40			
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.55			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.5\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.2	6.0	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			100	nA	
R_{Gint}	Internal Gate Resistance			7.5		Ω	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		374		ns	
t_r	Rise Time			50		ns	
$t_{d(off)}$	Turn-Off Delay Time			326		ns	
t_f	Fall Time			204		ns	
E_{on}	Turn-On Switching Loss				6.9		mJ
E_{off}	Turn-Off Switching Loss				5.2		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		419		ns	
t_r	Rise Time			63		ns	
$t_{d(off)}$	Turn-Off Delay Time			383		ns	
t_f	Fall Time			218		ns	
E_{on}	Turn-On Switching Loss				10.4		mJ
E_{off}	Turn-Off Switching Loss				5.9		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=100\text{A}, R_G=1.5\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		419		ns	
t_r	Rise Time			65		ns	
$t_{d(off)}$	Turn-Off Delay Time			388		ns	
t_f	Fall Time			222		ns	
E_{on}	Turn-On Switching Loss				11.5		mJ
E_{off}	Turn-Off Switching Loss				6.0		mJ

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.90	2.35	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		1.90		
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.90		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		5.1		μC
I_{RM}	Peak Reverse Recovery Current			45		A
E_{rec}	Reverse Recovery Energy			1.7		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		13.1		μC
I_{RM}	Peak Reverse Recovery Current			66		A
E_{rec}	Reverse Recovery Energy			4.9		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=100\text{A},$ $-di/dt=1600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		15.2		μC
I_{RM}	Peak Reverse Recovery Current			71		A
E_{rec}	Reverse Recovery Energy			5.7		mJ

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		30		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.65		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.278	K/W
	Junction-to-Case (per Diode)			0.418	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.167		K/W
	Case-to-Heatsink (per Diode)		0.250		
	Case-to-Heatsink (per Module)		0.050		
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		150		g

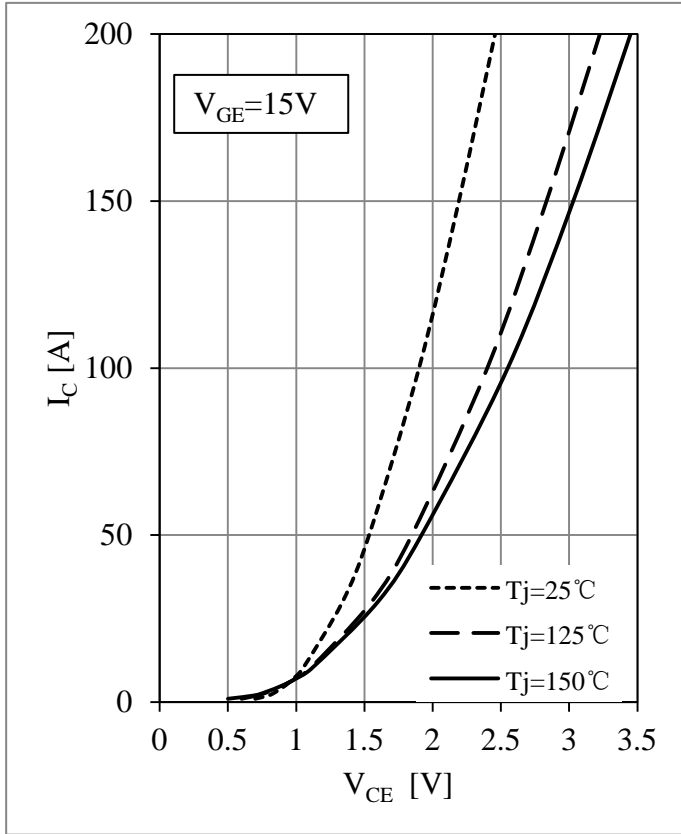


Fig 1. IGBT Output Characteristics

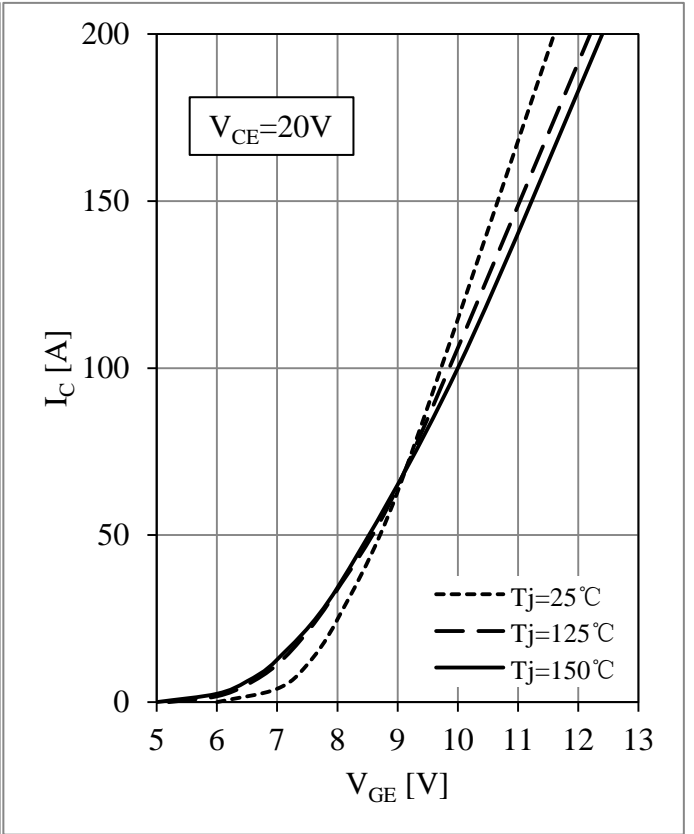


Fig 2. IGBT Transfer Characteristics

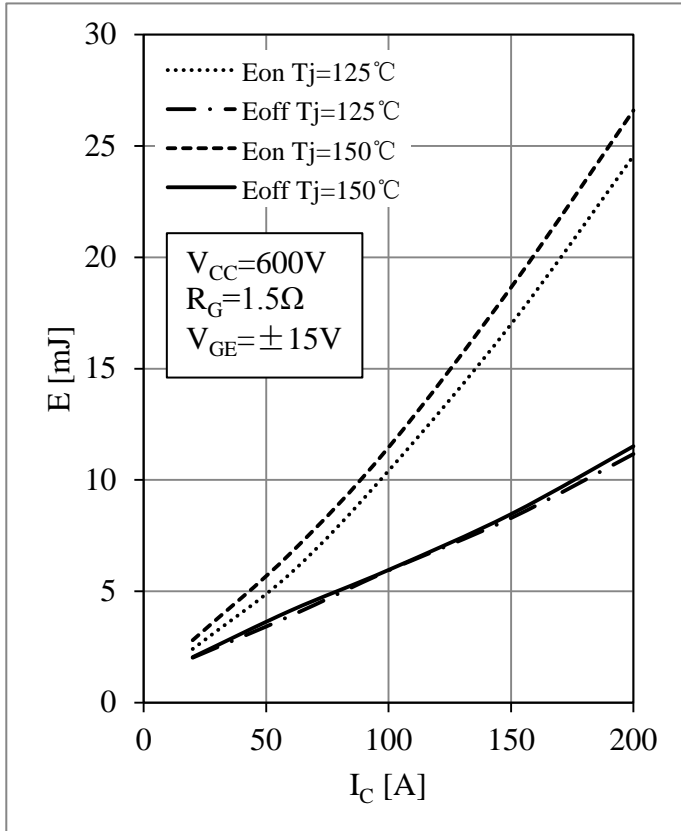


Fig 3. IGBT Switching Loss vs. I_C

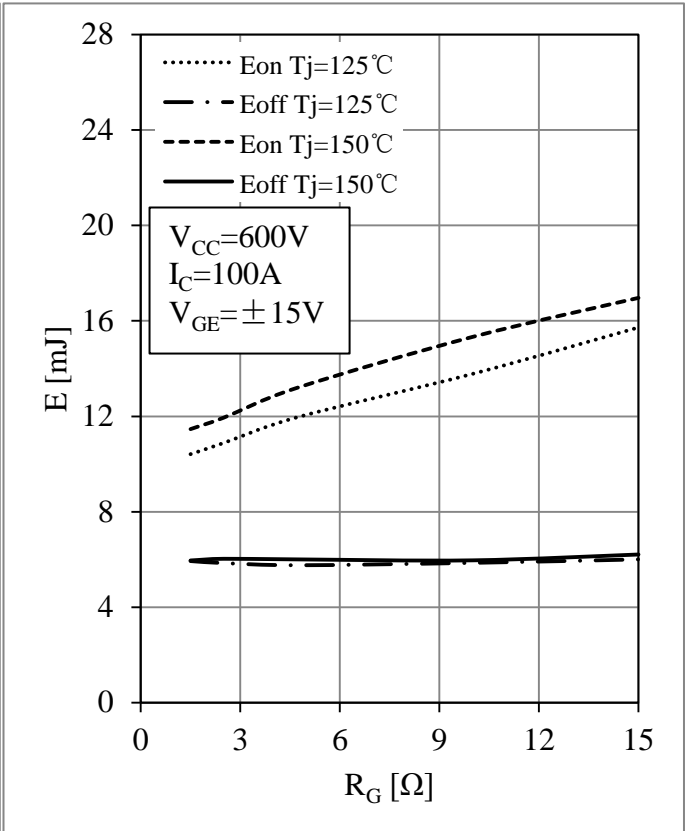


Fig 4. IGBT Switching Loss vs. R_G

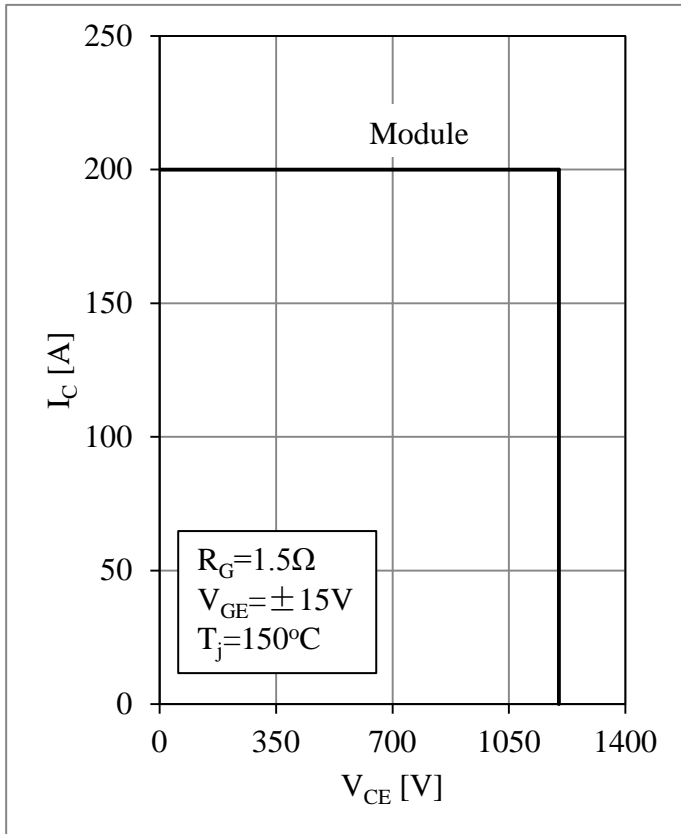


Fig 5. RBSOA

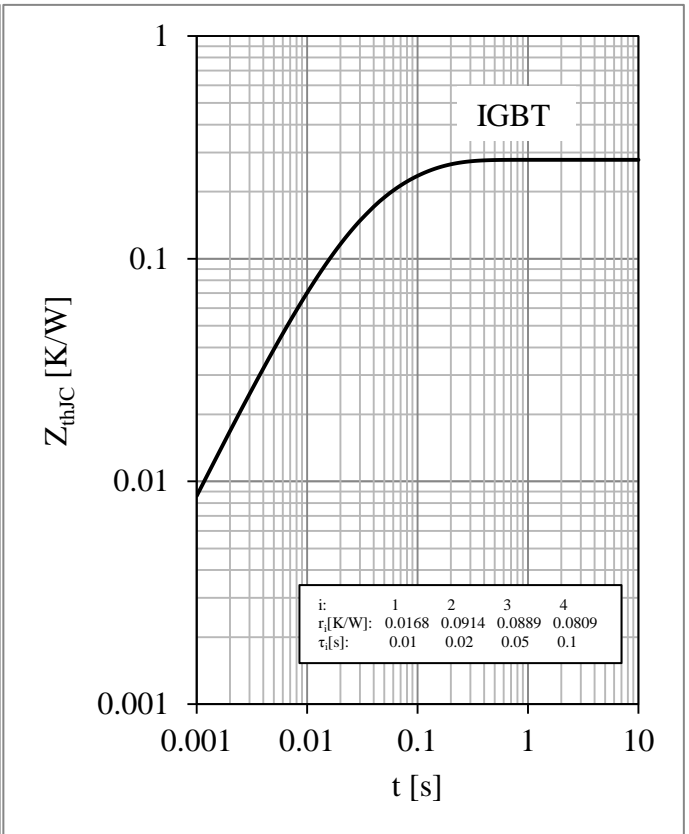


Fig 6. IGBT Transient Thermal Impedance

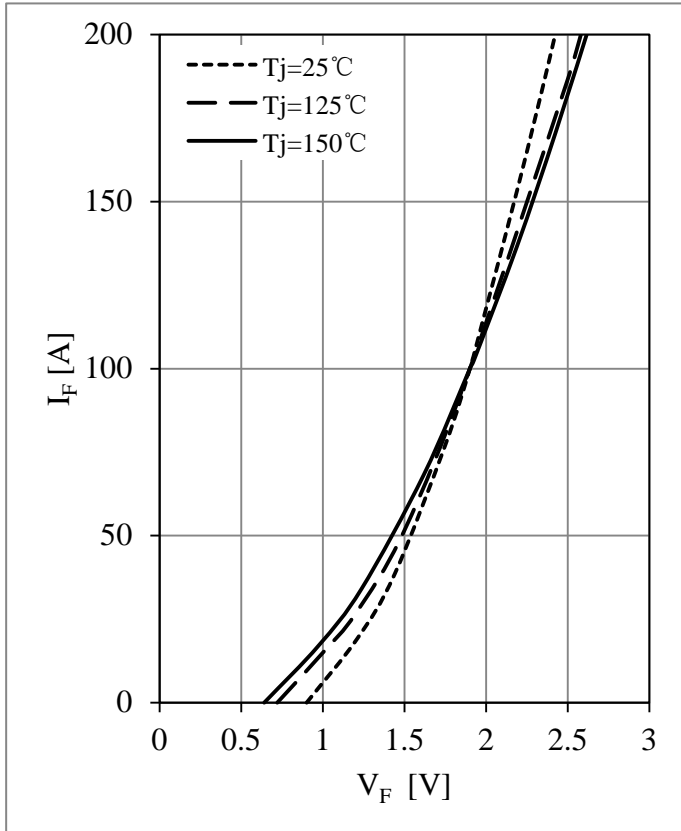


Fig 7. Diode Forward Characteristics

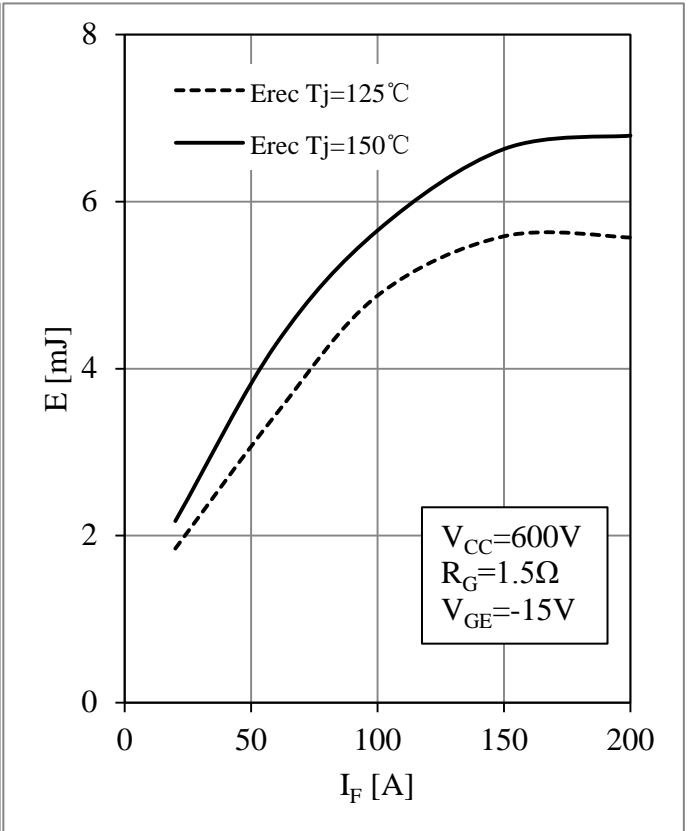


Fig 8. Diode Switching Loss vs. I_F

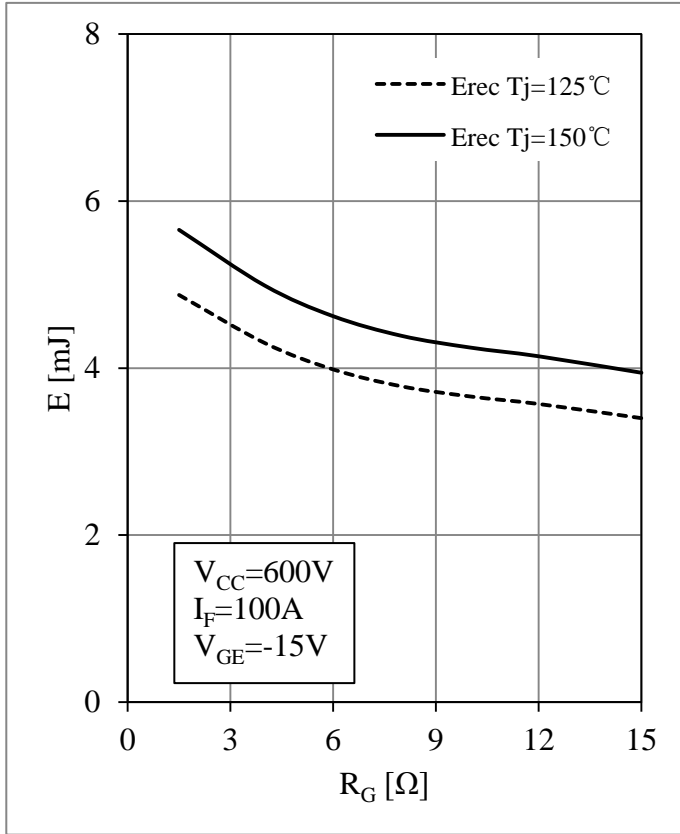


Fig 9. Diode Switching Loss vs. R_G

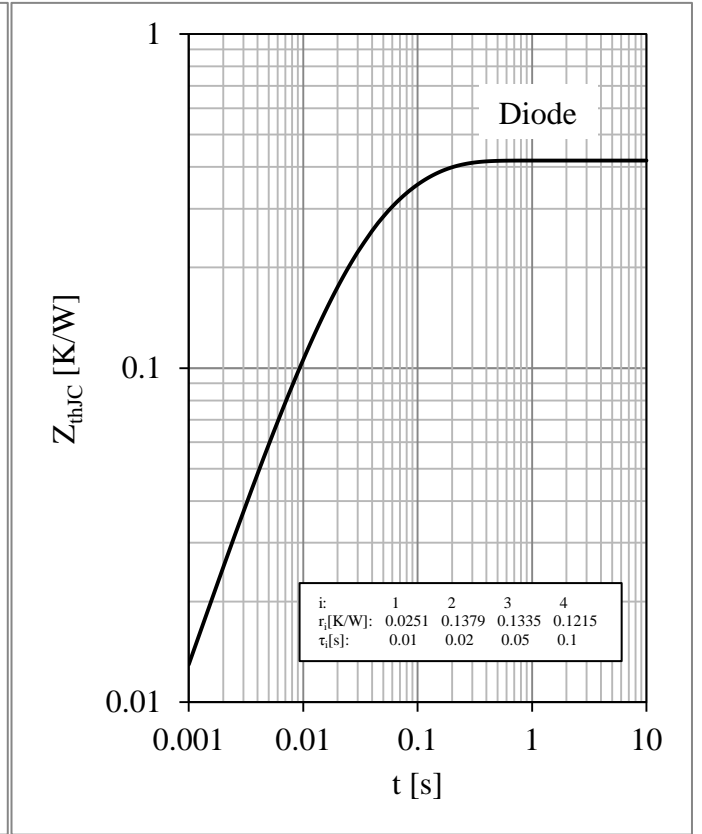
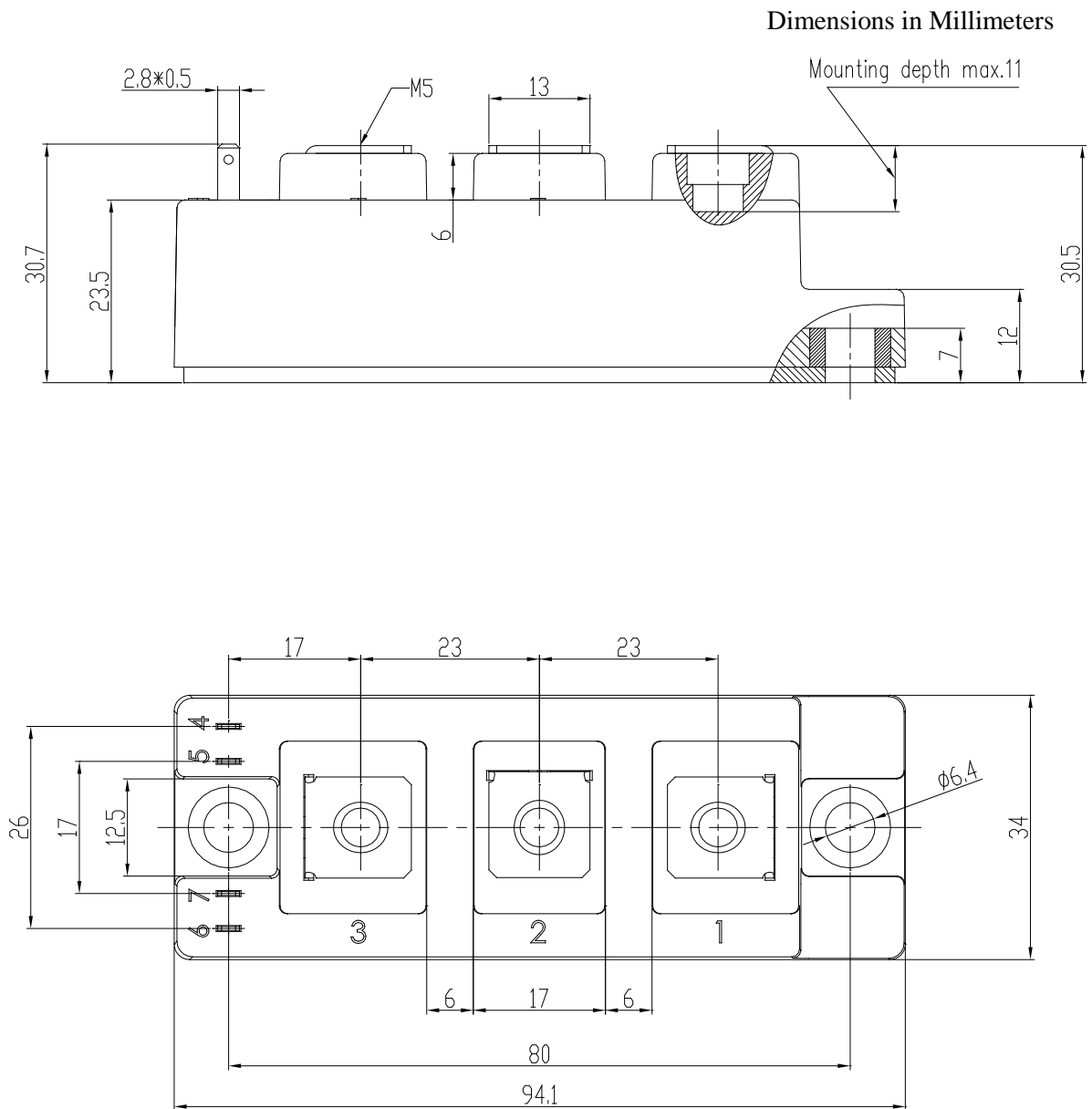


Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions



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